# NSN 5961-01-641-5820

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# Inclosure Material:

Ceramic and metal

# **Overall Length:**

Between 0.895 inches and 0.906 inches

# Semiconductor Material:

Silicon alloy

#### **Current Rating Per Characteristic:**

10.0 milliamperes emitter current, instantaneous

#### **Power Rating Per Characteristic:**

583.0 watts total power dissipation

#### Product Name:

Rf and microwave transistor

#### **Special Features:**

Designed for high power pulse iff, dme, and tacan; applications; 200 w (typ.) iff 1030 - 1090 mhz; 150 w (min.) dme 1025 - 1150 mhz; 140 w (typ.) tacan 960 - 1215 mhz; 8.2 db gain; refractory gold metallization; ballasting andlow thermal resistance for reliability and ruggedness; 30: 1 load vswr capability at specified operating conditions;

#### Shelf Life:

N/a

# Unit Of Measure:

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# Demilitarization:

No

#### Fiig:

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